



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
-30V	$9.5 \text{m}\Omega$ @ $V_{GS} = -10V$	-35A
	$17m\Omega$ @ $V_{GS} = -4.5V$	-25A

Features and Benefits

- Low R_{DS(ON)}—Ensures On-State Losses are Minimized
- Small form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

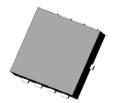
Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)

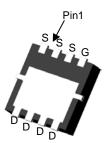
Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

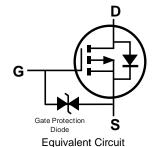




Top View



Bottom View



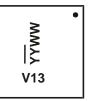
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3013SFV-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel
DMP3013SFV-13	PowerDI3333-8 (Type UX)	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



V13 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-12 -10	А
Continuous Drain Current (Note 7) $V_{GS} = -10V$ Steady $T_C = +25^{\circ}C$ State $T_C = +70^{\circ}C$			I _D	-35 -25	А
Maximum Continuous Body Diode Forward Curre	I _S	-35	Α		
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	-80	Α
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	-80	Α
Avalanche Current (Note 8) L = 1mH			I _{AS}	-14	Α
Avalanche Energy (Note 8) L = 1mH			E _{AS}	100	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.94	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{OJA}	134	°C/W
Total Power Dissipation (Note 6) T _A = +25°C		P_{D}	1.94	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{OJA}	65	°C/W
Total Power Dissipation (Note 7)	P_{D}	31	W	
Thermal Resistance, Junction to Case (Note 7)	R _{eJC}	4.0	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

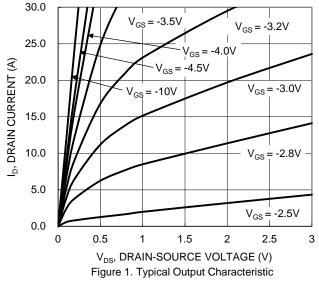
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)			- 714		0		
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)		•	•	•	•		
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	8	9.5	mΩ	$V_{GS} = -10V, I_D = -11.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	11	17	11122	$V_{GS} = -4.5V, I_D = -8.5A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V$, $I_S = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1674	_	pF	45)/)/ 0)/	
Output Capacitance	Coss	_	302	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	230	_	pF	7 = 1.0WHZ	
Gate Resistance	R_g	_	15.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg	_	16.2	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	33.7	_	nC	\\\\ 45\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q_{gs}	_	3.5	_	nC	$V_{DS} = -15V, I_{D} = -11.5A$	
Gate-Drain Charge	Q_{gd}	_	6.7	_	nC	7	
Turn-On Delay Time	t _{D(ON)}	_	4.0	_	ns		
Turn-On Rise Time	t _R	_	4.5	_	ns	$V_{DD} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	96	_	ns	$R_G = 6\Omega$, $I_D = -11.5A$	
Turn-Off Fall Time	t _F	_	106.5	_	ns		
Reverse Recovery Time	t _{RR}	_	46	_	ns	1 44.50 41/44 4000///-	
Reverse Recovery Charge	Q_{RR}		25.5		nC	$I_S = -11.5A$, $dI/dt = 100A/\mu s$	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_{J} = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

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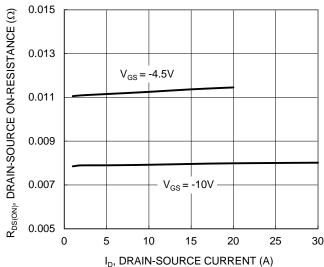


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

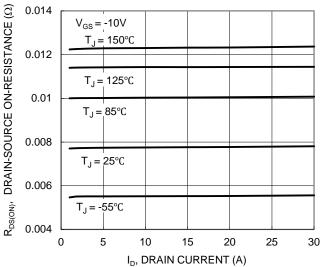
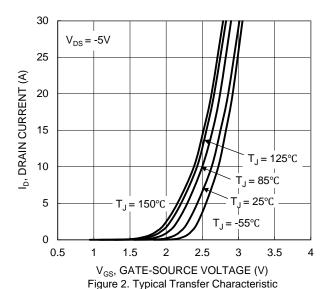


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



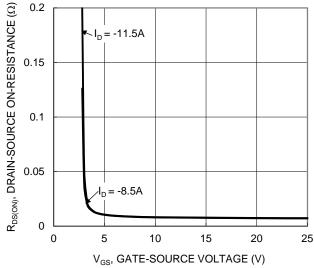
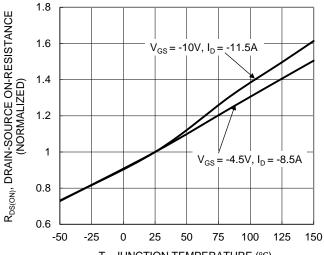


Figure 4. Typical Transfer Characteristic



T_J, JUNCTION TEMPERATURE (°C)
Figure 6. On-Resistance Variation with Junction
Temperature



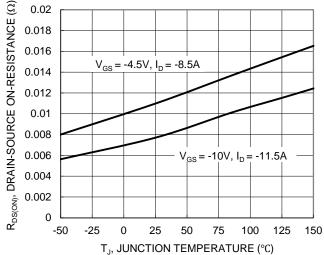
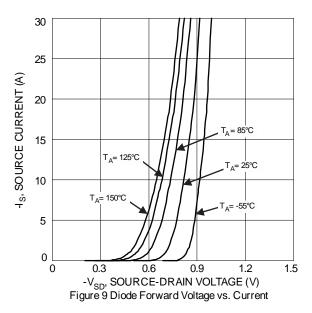


Figure 7. On-Resistance Variation with Junction Temperature



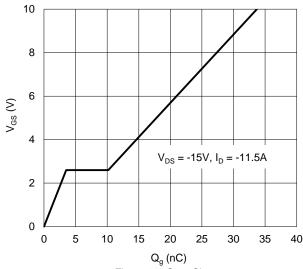


Figure 11. Gate Charge

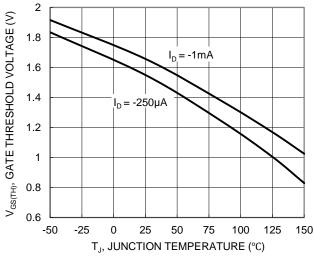
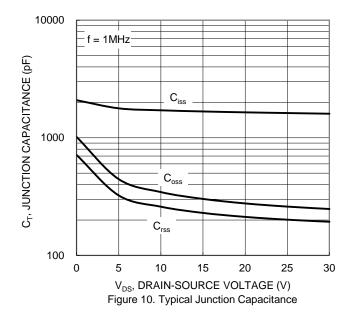


Figure 8. Gate Threshold Variation vs. Junction Temperature



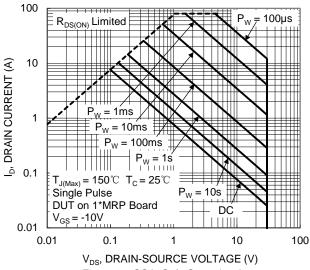


Figure 12. SOA, Safe Operation Area

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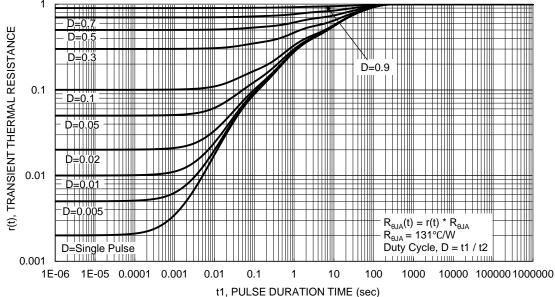
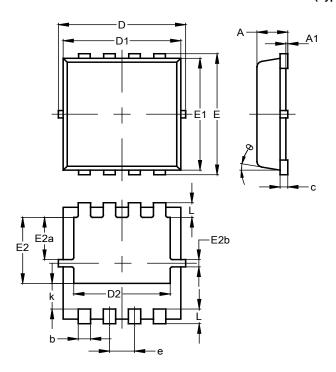


Figure 13. Transient Thermal Resistance



Package Outline Dimensions

PowerDI3333-8 (Type UX)

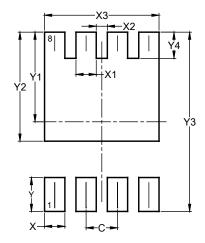


PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		

June 2019



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